

Silicon NPN Power Transistors

2SD2300

DESCRIPTION

- With TO-3PFM package
- High breakdown voltage
- Built-in damper diode

APPLICATIONS

- For color TV horizontal output deflection applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

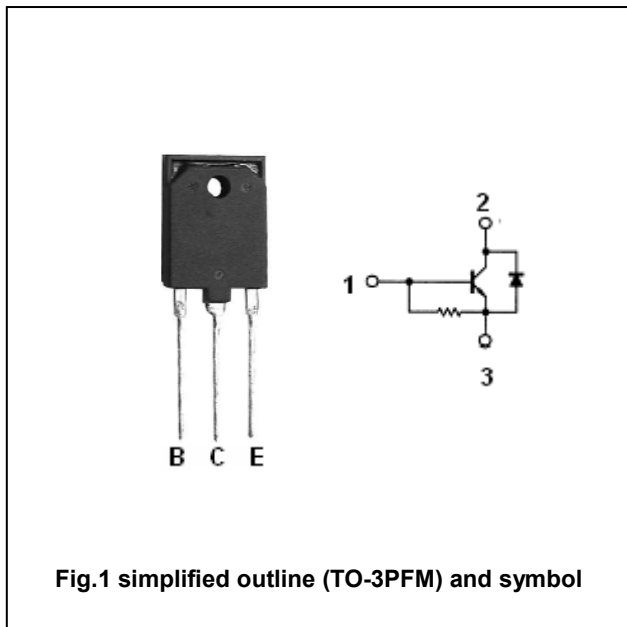


Fig.1 simplified outline (TO-3PFM) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		6	A
I _{C(surge)}	Collector surge current		16	A
P _C	Collector power dissipation	T _C =25□	50	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

Silicon NPN Power Transistors

2SD2300

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =350mA, I _C =0	6			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =4.5A; I _B =1.2A			5.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =4.5A; I _B =1.2A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =1500V; R _{BE} =0			500	μA
h _{FE}	DC current gain	I _C =1A; V _{CE} =5V			20	
t _f	Fall time	I _C =4A; I _{B1} =0.8A; I _{B2} ≈-1.5A			1.0	μs
V _F	Diode forward voltage	I _F =6A			3.0	V

Silicon NPN Power Transistors

2SD2300

PACKAGE OUTLINE

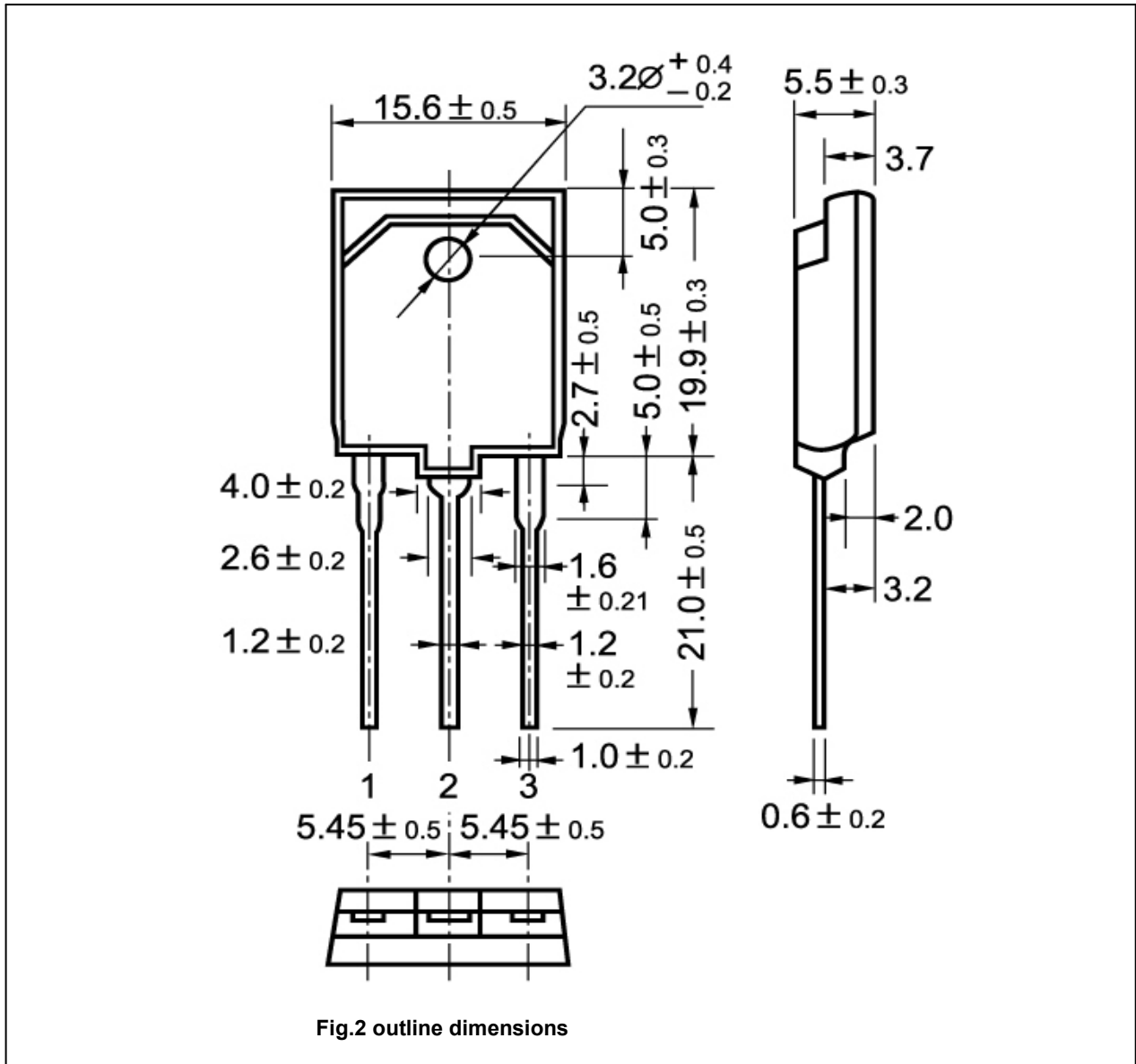


Fig.2 outline dimensions